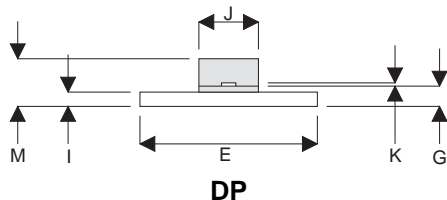
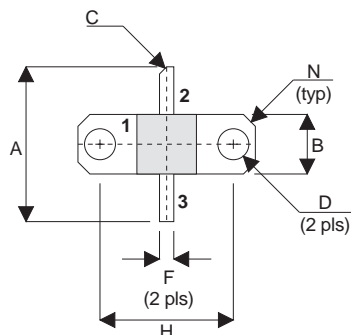


MECHANICAL DATA



PIN 1 SOURCE PIN 2 DRAIN  
PIN 3 GATE

DIM	mm	Tol.	Inches	Tol.
A	16.51	0.25	0.650	0.010
B	6.35	0.13	0.250	0.005
C	45°	5°	45°	5°
D	3.30	0.13	0.130	0.005
E	18.92	0.08	0.745	0.003
F	1.52	0.13	0.060	0.005
G	2.16	0.13	0.085	0.005
H	14.22	0.08	0.560	0.003
I	1.52	0.13	0.060	0.005
J	6.35	0.13	0.250	0.005
K	0.13	0.03	0.005	0.001
M	5.08	0.51	0.200	0.020
N	1.27 x 45°	0.13	0.050 x 45°	0.005

**GOLD METALLISED  
MULTI-PURPOSE SILICON  
DMOS RF FET  
40W – 28V – 500MHz  
SINGLE ENDED**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW  $C_{rss}$
- USEFUL  $P_O$  AT 1GHz
- LOW NOISE
- HIGH GAIN – 12 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS  
from 1 MHz to 500 MHz

ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$P_D$	Power Dissipation	87.5W
$BV_{DSS}$	Drain – Source Breakdown Voltage	70V
$BV_{GSS}$	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	10A
$T_{stg}$	Storage Temperature	-65 to 150°C
$T_j$	Maximum Operating Junction Temperature	200°C

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
B <sub>V</sub> DSS Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0      I <sub>D</sub> = 100mA	70			V
I <sub>D</sub> DSS Zero Gate Voltage Drain Current	V <sub>DS</sub> = 28V      V <sub>GS</sub> = 0			2	mA
I <sub>G</sub> DSS Gate Leakage Current	V <sub>GS</sub> = 20V      V <sub>DS</sub> = 0			1	μA
V <sub>GS(th)</sub> Gate Threshold Voltage*	I <sub>D</sub> = 10mA      V <sub>DS</sub> = V <sub>GS</sub>	1		7	V
g <sub>fs</sub> Forward Transconductance*	V <sub>DS</sub> = 10V      I <sub>D</sub> = 2A	1.6			S
G <sub>PS</sub> Common Source Power Gain	P <sub>O</sub> = 40W	12			dB
η Drain Efficiency	V <sub>DS</sub> = 28V      I <sub>DQ</sub> = 0.2A	50			%
VSWR Load Mismatch Tolerance	f = 500MHz	20:1			—
C <sub>iss</sub> Input Capacitance	V <sub>DS</sub> = 0      V <sub>GS</sub> = -5V      f = 1MHz			120	pF
C <sub>oss</sub> Output Capacitance	V <sub>DS</sub> = 28V      V <sub>GS</sub> = 0      f = 1MHz			60	pF
C <sub>rss</sub> Reverse Transfer Capacitance	V <sub>DS</sub> = 28V      V <sub>GS</sub> = 0      f = 1MHz			5	pF

\* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

## HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

## THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 2.0°C / W
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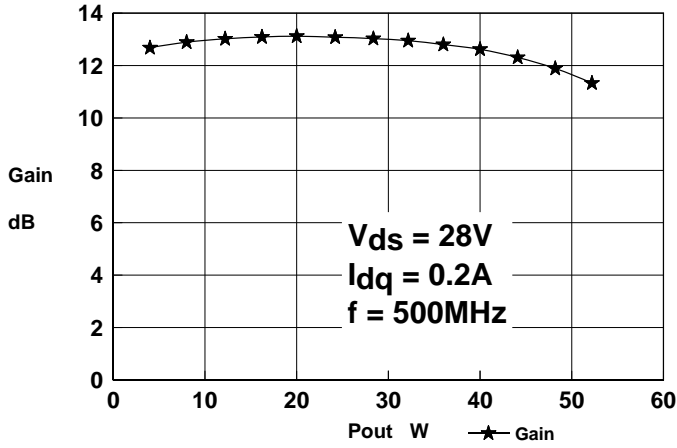


Figure 1- Gain vs. Power Output

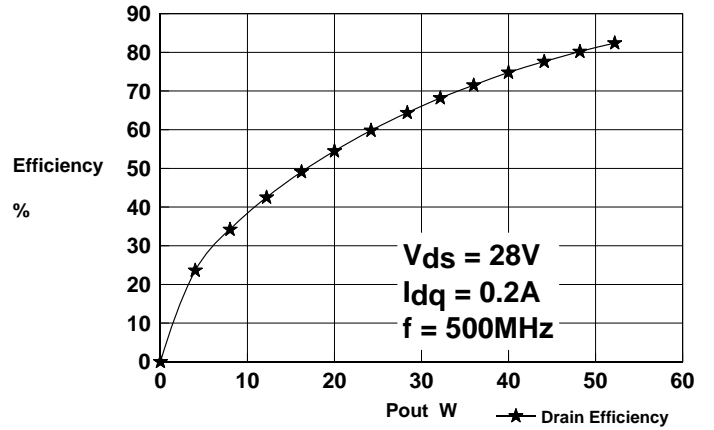


Figure 2 - Efficiency vs Power Output

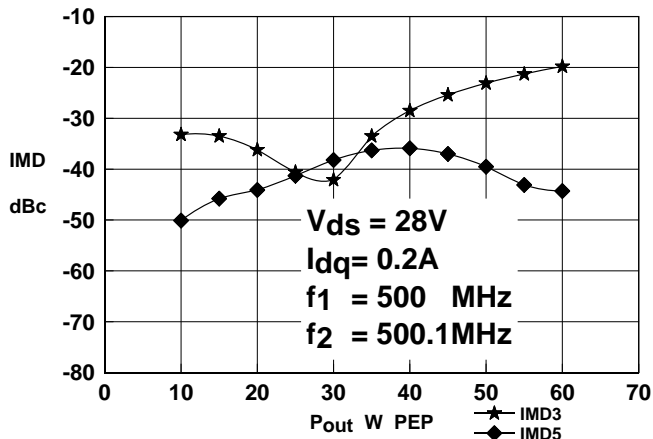


Figure 3 - IMD vs Power Output

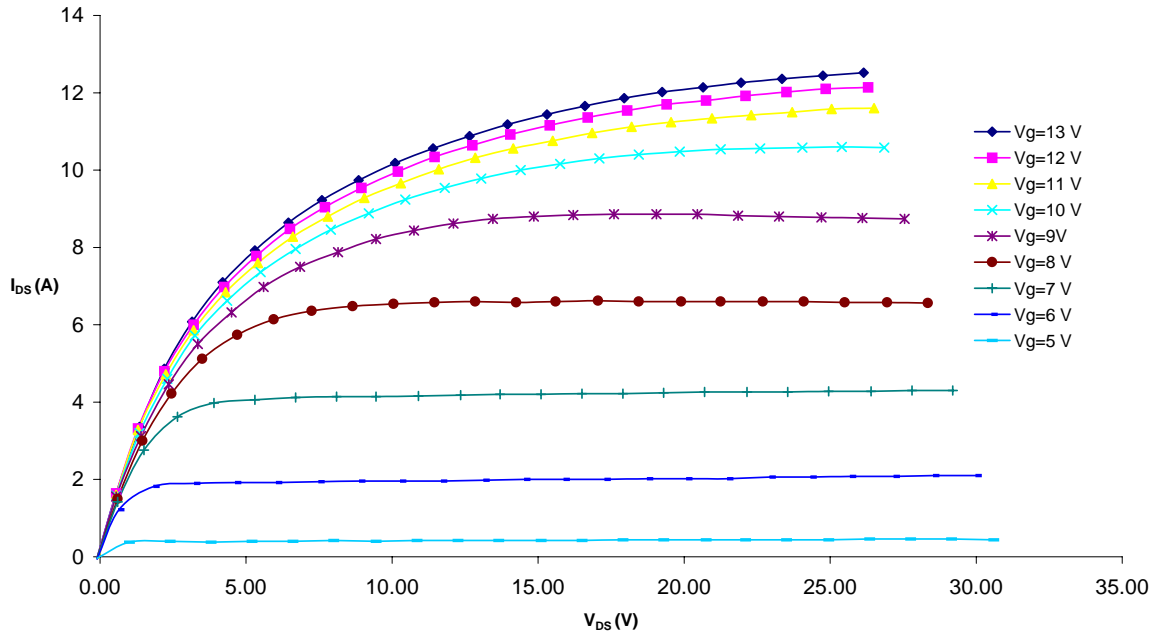
OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z <sub>S</sub> Ω	Z <sub>L</sub> Ω
500MHz	2.3 + j1.0	3.7 + j0.8

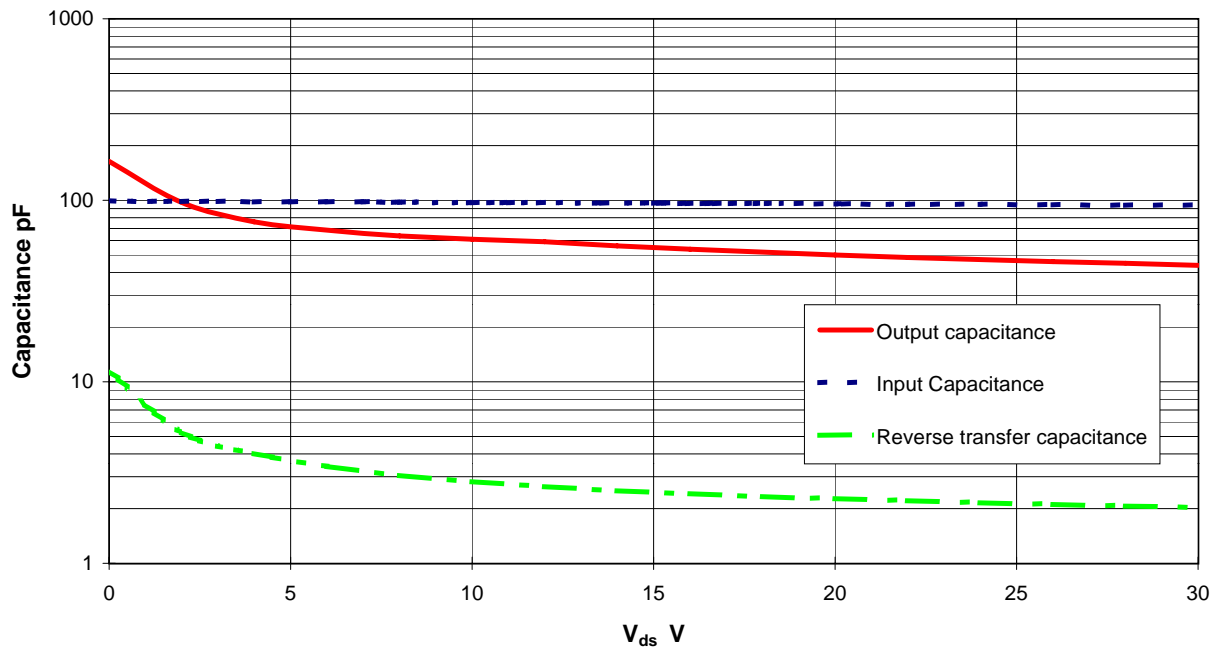
Typical S Parameters

! V<sub>DS</sub> = 28V, I<sub>DQ</sub> = 0.2A  
 # MHZ S M A R 50

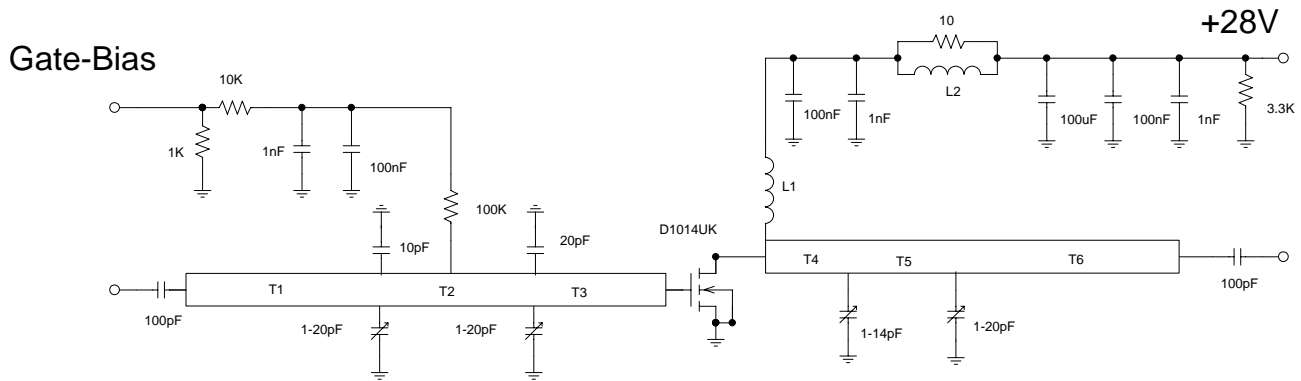
Freq MHz	S11		S21		S12		S22	
	mag	ang	mag	ang	mag	ang	mag	ang
100	0.79	-158	14.62	69	0.012	-7	0.61	-145
200	0.88	-167	5.82	42	0.006	3	0.79	-156
300	0.92	-171	3.02	28	0.007	60	0.87	-162
400	0.92	-176	1.82	18	0.117	77	0.90	-167
500	0.94	-179	1.44	15	0.017	76	0.92	-169
600	0.95	177	1.06	13	0.023	75	0.95	-171
700	0.97	174	0.68	10	0.029	74	0.97	-174
800	0.97	171	0.54	5	0.034	69	0.96	-177
900	0.98	167	0.45	1	0.039	64	0.97	178
1000	0.97	165	0.36	1	0.043	64	0.96	178



**Figure 4 – Typical IV Characteristics.**



**Figure 5 – Typical CV Characteristics.**



Substrate 0.8mm G200, Er=4.0

All microstrip lines W=1.68mm

T1 36mm  
 T2 16mm  
 T3 10mm  
 T4 6.5mm  
 T5 12mm  
 T6 39mm

L1 5.5 turns 20swg enamelled copper wire, 7mm i.d.

L2 1.5 turns 24swg enamelled copper wire on Siemens B62152A7X 2 hole core

## D1014UK 500MHz Test Fixture